

an impurity is from the center in the direction of thickness of said channel region to an interface between the channel region and a layer located on said substrate side.

9. (Amended) A method of manufacturing a thin-film transistor according to Claim 1, characterized in that a process of introducing said impurity to said channel region is carried out by impurity diffusion from an impurity diffusion source arranged at a lower layer side of said channel region.

11. (Amended) A method of manufacturing a thin-film transistor according to Claim 4, characterized in that said crystallization process is laser annealing on a semiconductor film so as to form said channel region.

12. (Amended) A method of manufacturing a thin-film transistor according to Claim 1, characterized in that each process carried out after introducing said impurities to said channel region is carried out at a temperature below 400°C.

13. (Amended) A method of manufacturing a thin-film transistor according to Claim 1, characterized in that each process carried out after introducing said impurities to said channel region is carried out at a temperature below 300°C.